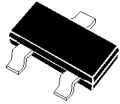


CMPT8099 NPN
CMPT8599 PNP

COMPLEMENTARY
SILICON TRANSISTOR



SOT-23 CASE

CentralTM

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT8099, CMPT8599 types are Complementary Silicon Transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for general purpose audio amplifier applications.

Marking Codes are CKB and C2W
Respectively.

MAXIMUM RATINGS (T_A=25°C)

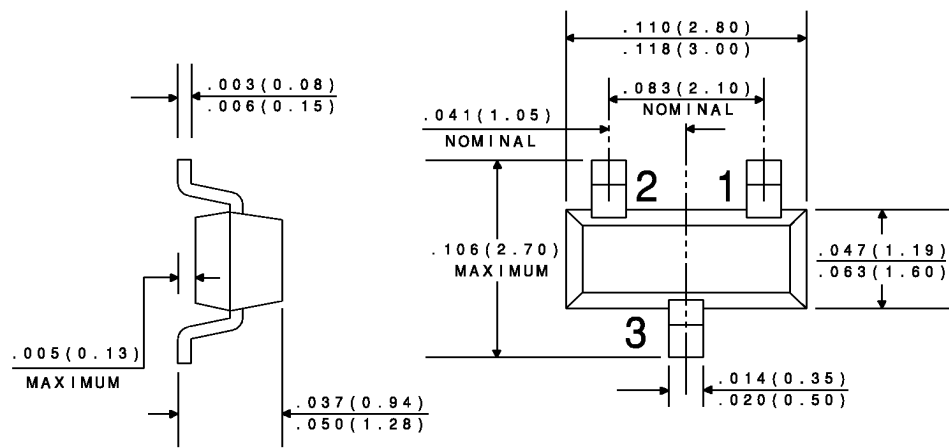
	SYMBOL	CMPT8099	CMPT8599	UNITS
Collector-Base Voltage	V _{CB0}	80	80	V
Collector-Emitter Voltage	V _{CEO}	80	80	V
Emitter-Base Voltage	V _{EBO}	6.0	5.0	V
Collector Current	I _C	500		mA
Power Dissipation	P _D	350		mW
Operating and Storage				
Junction Temperature	T _J , T _{stg}	-65 to +150		°C
Thermal Resistance	θ _{JA}	357		°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	CMPT8099		CMPT8599		UNITS
		MIN	MAX	MIN	MAX	
I _{CBO}	V _{CB} =80V		0.1		0.1	mA
I _{EBO}	V _{BE} =6.0V		0.1		-	mA
I _{EBO}	V _{BE} =4.0V		-		0.1	mA
BV _{CB0}	I _C =100mA	80		80		V
BV _{CEO}	I _C =10mA	80		80		V
BV _{EBO}	I _E =10mA	6.0		5.0		V
V _{CE(SAT)}	I _C =100mA, I _B =5.0mA		0.4		0.4	V
V _{CE(SAT)}	I _C =100mA, I _B =10mA		0.3		0.3	V
V _{BE(ON)}	V _{CE} =5.0V, I _C =10mA	0.6	0.8	0.6	0.8	V
h _{FE}	V _{CE} =5.0V, I _C =1.0mA	100	300	100	300	
h _{FE}	V _{CE} =5.0V, I _C =10mA	100		100		

SYMBOL	TEST CONDITIONS	CMPT8099		CMPT8599		UNITS
		MIN	MAX	MIN	MAX	
h_{FE}	$V_{CE}=5.0V, I_C=100mA$	75		75		
f_T	$V_{CE}=5.0V, I_C=10mA, f=100MHz$	150		150		MHz
C_{ob}	$V_{CB}=10V, I_E=0, f=1.0MHz$		6.0		4.5	pF
C_{ib}	$V_{BE}=0.5V, I_C=0, f=1.0MHz$		25		30	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR